## P-Channel 100-V (D-S) MOSFET

### **Key Features:**

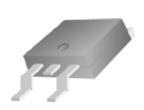
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

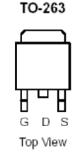
### **Typical Applications:**

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
-100	19 @ V <sub>GS</sub> = -10V	-90 <sup>a</sup>		
-100	21 @ V <sub>GS</sub> = -4.5V	-90		







ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter			Limit	Units			
Drain-Source Voltage			-100	V			
Gate-Source Voltage		$V_{GS}$	±20	V			
Continuous Drain Current a	T <sub>C</sub> =25°C	$I_D$	-90	Α			
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	-360	^			
Continuous Source Current (Diode Conduction) a	T <sub>C</sub> =25°C	I <sub>S</sub>	-90	Α			
Power Dissipation <sup>a</sup>	T <sub>C</sub> =25°C	$P_{D}$	300	W			
Operating Junction and Storage Temperature Range		$T_J,T_stg$	-55 to 175	°C			

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient °	$R_{\theta JA}$	11	°C/W			
Maximum Junction-to-Case	$R_{\theta JC}$	0.5	C/VV			

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#### Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

#### **Electrical Characteristics**

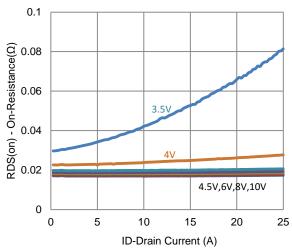
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit		
Static								
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA		
Zero Gate Voltage Drain Current		$V_{DS} = -80 \text{ V}, V_{GS} = 0 \text{ V}$			-1 -10 uA			
Zero Gate Voltage Brain Current	I <sub>DSS</sub>	$V_{DS} = -80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$						
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-110			Α		
Drain Cauras On Basistanas a	r	$V_{GS} = -10 \text{ V}, I_{D} = -25 \text{ A}$			19	mΩ		
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, I_{D} = -20 \text{ A}$			21	11122		
Forward Transconductance a	g <sub>fs</sub>	$V_{DS} = -15 \text{ V}, I_{D} = -25 \text{ A}$		75		S		
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = -45 \text{ A}, V_{GS} = 0 \text{ V}$		-0.95		V		
		Dynamic <sup>b</sup>						
Total Gate Charge	$Q_g$	$V_{DS} = -50 \text{ V}, V_{GS} = -4.5 \text{ V},$		164		nC		
Gate-Source Charge	$Q_{gs}$	$I_{DS} = -30 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_{D} = -20 \text{ A}$		50				
Gate-Drain Charge	$Q_gd$	10 = 20 A		63				
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = -50 \text{ V}, R_1 = 2.5 \Omega,$		39				
Rise Time	t <sub>r</sub>	$V_{DS} = -30 \text{ V}, K_L - 2.3 \Omega,$ $I_D = -20 \text{ A},$		104		ns		
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		217				
Fall Time	t <sub>f</sub>	VGEN = 10 V, NGEN = 0 12		89				
Input Capacitance	C <sub>iss</sub>			15378				
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		774		pF		
Reverse Transfer Capacitance	$C_{rss}$			530				

#### Notes

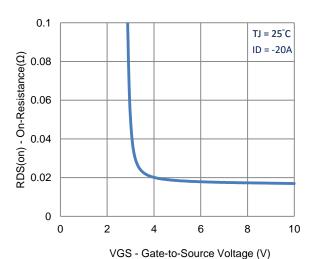
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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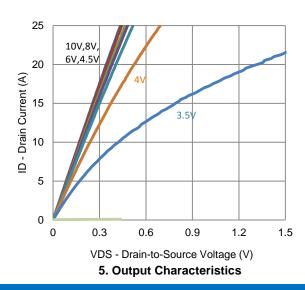
### **Typical Electrical Characteristics**



#### 1. On-Resistance vs. Drain Current

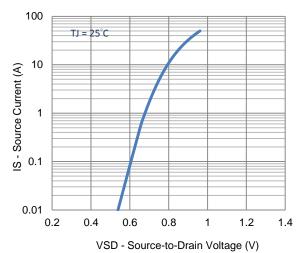


3. On-Resistance vs. Gate-to-Source Voltage

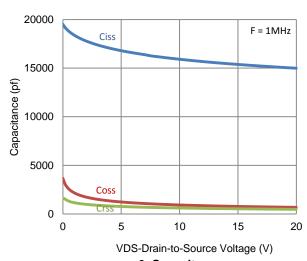


25 20 20 20 15 0 0 1 2 3 4 5 6 VGS - Gate-to-Source Voltage (V)

2. Transfer Characteristics



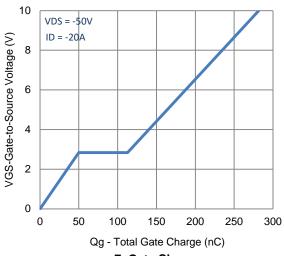
4. Drain-to-Source Forward Voltage



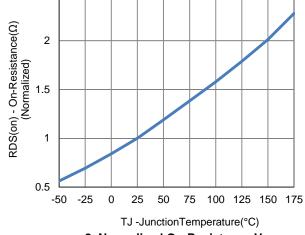
6. Capacitance

### **Typical Electrical Characteristics**

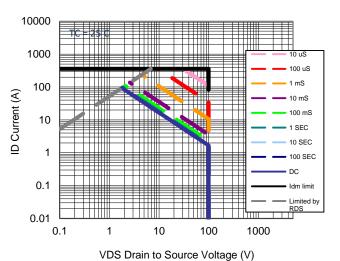
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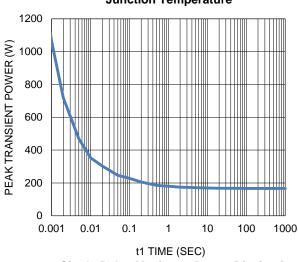
7. Gate Charge



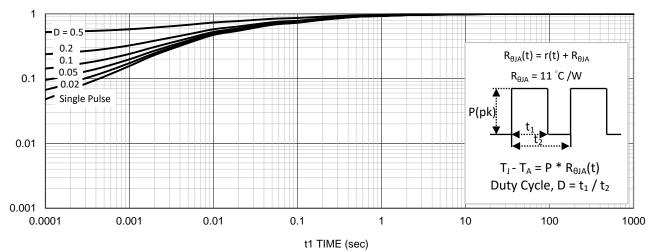
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area

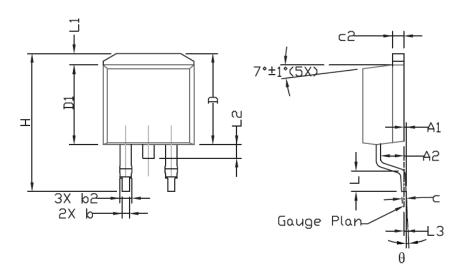


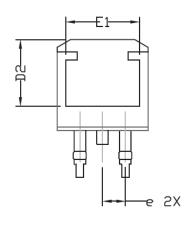
10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

# Package Information





SVMDEII	DIMENS:	ONAL F	REQMTS	INCH	ES REG	2TM		
SYMBOL	MIN	NDM	MAX	MIN	NDM	MAX		
A	4,30	4 <b>.</b> 57	4.72	0.169	0.180	0.186		
A1	0		0,25	0		0.010		
A2	2,47	2.57	2,67	0.097	0.101	0.105		
b	0.69	0,813	0.94	0.027	0.032	0.037		
b2	1.17	1.27	1,45	0.046	0.050	0.057		
С	0.48	0,50	0,60	0.019	0.020	0.024		
c2	1,17	1.27	1,37	0.046	0.050	0,054		
D	9,80	10.05	10,30	0.386	0,396	0.406		
D1	8,64	8.78	9,65	0,340	0.346	0,380		
D2	7.12	7.37	7,62	0.280	0.290	0,300		
E	9,70	10.15	10.54	0,382	0.400	0.415		
E1	8,00	8.20	8,40	0,315	0.323	0,331		
е	2,	54 BSC	,	0.3	0.100 BSC			
H	14,99	15.24	15,49	0.590	0.600	0.610		
L	1,78	2.29	2.79	0.070	0.090	0.110		
L1	1.02	1.27	1.52	0.040	0.050	0,060		
L2			1.75			0.069		
L3		0,254			0.010			
А	n∘		8*	U+		8*		